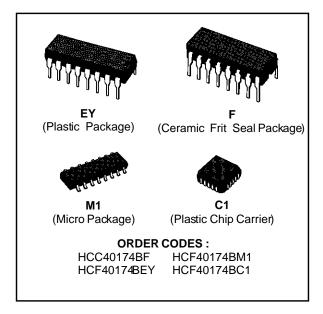


HCC/HCF40174B

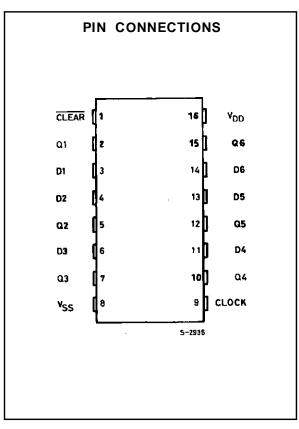
HEX "D" - TYPE FLIP-FLOP

- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT SPECIFIED AT 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18 V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TEN-TATIVE STANDARD N°. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



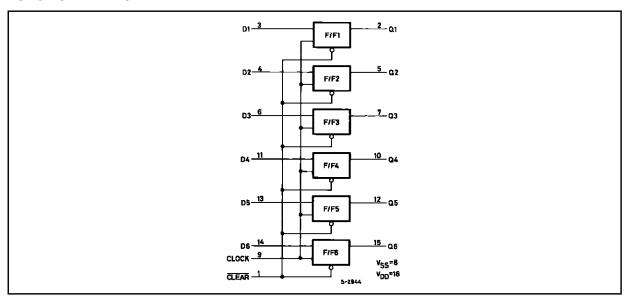
DESCRIPTION

The **HCC40174B** (extended temperature range) and **HCF40174B** (intermediate temperature range) are monolithic integrated circuits available in 16-lead dual in-line plastic or ceramic package and plastic micro package.



June 1989 1/12

FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V V
Vi	Input Voltage	- 0.5 to V _{DD} + 0.5	V
l ₁	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T_{op} = Full Package-temperature Range	200 100	mW mW
Top	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

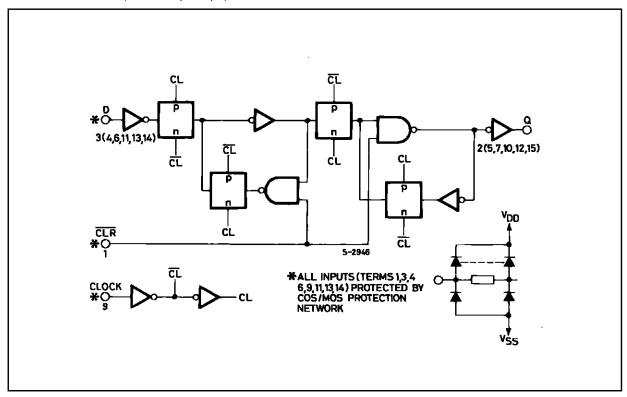
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage: HCC Types	3 to 18	V
	HCF Types	3 to 15	V
V_{I}	Input Voltage	0 to V _{DD}	V
Top	Operating Temperature : HCC Types	– 55 to + 125	°C
	HCF Types	- 40 to + 85	°C



LOGIC DIAGRAM (1 of 6 Flip-Flops)



TRUTH TABLE

	Output		
Clock	Data	Clear	Q
	0	1	0
	1	1	1
	Х	1	NC
Х	Х	0	0

1 = High Level

X = Don't Care

0 = Low Level

NC = No Change

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

			Т	est Con	dition	s	Value							
Symbol	Symbol Parameter		V _I V _O	IIOI VDD	V _{DD}	ΤL	o w*	25°C			T _{High} *		Unit	
			(V)	(V)	(μA)	(V)	Min.	Max.	Min.	Тур.	Max.	Min.	Max.	
ΙL	Quiescent		0/ 5			5		1		0.02	1		30	
	Current HCC	0/10			10		2		0.02	2		60		
		Types	0/15			15		4		0.02	4		120	
			0/20			20		20		0.04	20		600	μΑ
			0/ 5			5		4		0.02	4		30	
		HCF Types	0/10			10		8		0.02	8		60	
		Турез	0/15			15		16		0.02	16		120	
V _{OH}	Output High	า	0/ 5		< 1	5	4.95		4.95			4.95		
	Voltage		0/10		< 1	10	9.95		9.95			9.95		V
			0/15		< 1	15	14.95		14.95			14.95		
V _{OL}	Output Low	1	5/0		< 1	5		0.05			0.05		0.05	
	Voltage		10/0		< 1	10		0.05			0.05		0.05	V
			15/0		< 1	15		0.05			0.05		0.05	
V _{IH}	Input High			0.5/4.5	< 1	5	3.5		3.5			3.5		
	Voltage			1/9	< 1	10	7		7			7		V
				1.5/13.5	< 1	15	11		11			11		
V_{IL}	Input Low			4.5/0.5	< 1	5		1.5			1.5		1.5	
	Voltage			9/1	< 1	10		3			3		3	V
				13.5/1.5	< 1	15		4			4		4	
I _{OH}	Output		0/ 5	2.5		5	- 2		- 1.6	- 3.2		- 1.15		
	Drive Current	HCC	0/ 5	4.6		5	- 0.64		- 0.51	- 1		- 0.36		
	Current	Types	0/10	9.5		10	- 1.6		- 1.3	- 2.6		- 0.9		
			0/15	13.5		15	- 4.2		- 3.4	- 6.8		- 2.4		mA
			0/ 5	2.5		5	- 1.53		- 1.36	- 3.2		- 1.1		1117 (
		HCF	0/ 5	4.6		5	- 0.52		- 0.44	- 1		- 0.36		
		Types	0/10	9.5		10	- 1.3		- 1.1	- 2.6		- 0.9		
			0/15	13.5		15	- 3.6		- 3.0	- 6.8		- 2.4		
I_{OL}	Output	1100	0/ 5	0.4		5	0.64		0.51	1		0.36		
	Sink Current	HCC Types	0/10	0.5		10	1.6		1.3	2.6		0.9		
	Current	.) 00	0/15	1.5		15	4.2		3.4	6.8		2.4		mA
			0/ 5	0.4		5	0.52		0.44	1		0.36		1117 (
		HCF Types	0/10	0.5		10	1.3		1.1	2.6		0.9		
		.,,,,,,,	0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input HCC Leakage Types		0/18	Any In	put	18		± 0.1		±10 ⁻⁵	± 0.1		± 1	μΑ
	Current	HCF Types	0/15			15		± 0.3		±10 ⁻⁵			± 1	
Cı	Input Capa	citance		Any In	put					5	7.5			pF

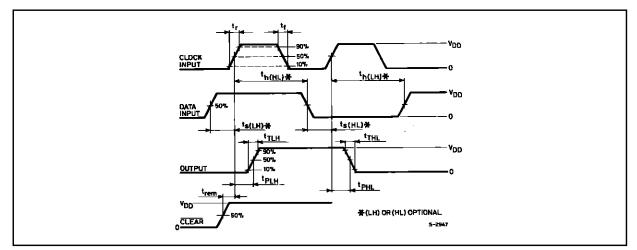
^{*} $T_{Low} = -55^{\circ}\text{C}$ for HCC device : -40°C for HCF device. * $T_{High} = +125^{\circ}\text{C}$ for HCC device : $+85^{\circ}\text{C}$ for HCF device. The Noise Margin for both "1" and "0" level is : 1V min. with $V_{DD} = 5V$, 2V min. with $V_{DD} = 10V$, 2.5 V min. with $V_{DD} = 15V$.



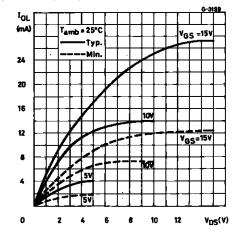
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}C$, $C_{L} = 50 pF$, $R_{L} = 200 k\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\%/^{\circ}C$, all input rise and fall time = 20ns)

Comple al	Damamatan	Test Conditions			I Imia		
Symbol	Parameter —		V _{DD} (V)	Min.	Тур.	Max.	Unit
t _{PLH} ,	Propagation Delay Time		5		150	300	
t_{PHL}	Clock to Output		10		70	140	ns
			15		50	100	
t _{PHL}	Propagation Delay Time		5		100	200	
	Clear to Output		10		50	100	ns
			15		40	80	
t _{THL} ,	Transition Time		5		100	200	
t_{TLH}			10		50	100	ns
			15		40	80	
t _{setup} Data	Data Setup Time		5	40	20		
			10	20	10		ns
			15	10	0		
t _{hold} Data Ho	Data Hold Time		5	80	40		
			10	40	20		ns
			15	30	15		
t _W	Clock Input Pulse Width		5	130	65		
	Low Level		10	60	30		ns
			15	40	20		
t _W	Clock Input Pulse Width		5	130	65		
	High Level		10	60	30		ns
			15	40	20		
t _W	Clear Input Pulse Width		5	100	50		
	Low Level		10	50	25		ns
			15	40	20		
t _r , t _f	Clock Input Rise or Fall Time		5			15	
			10			15	μs
			15			15	
t _{rem}	Clear Removal Time		5	0	- 40		
			10	0	- 15		ns
			15	0	- 10		
f _{CL}	Maximum Clock Input Frequency		5	3.5	7		
			10	6	12		MHz
			15	8	16		

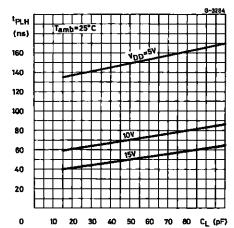
WAVEFORMS



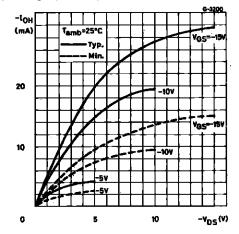
Output Low (sink) Current Characteristics.



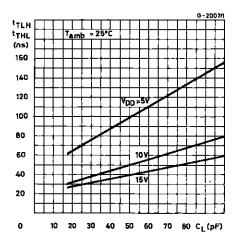
Typical Propagation Delay Time (clock to output) vs. Load Capacitance.



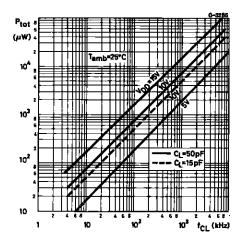
Output High (source) Current Characteristics.



Typical Transition Time vs. Load Capacitance.

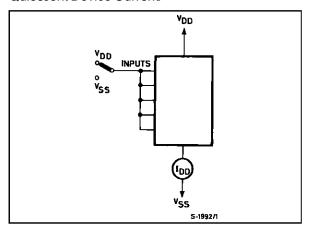


Typical Dynamical Power Dissipation vs. Clock Frequency.

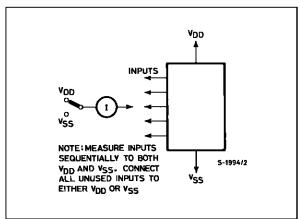


TEST CIRCUITS

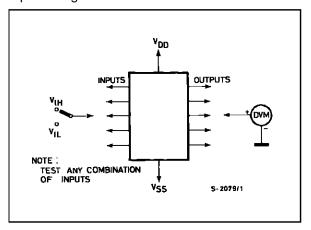
Quiescent Device Current.



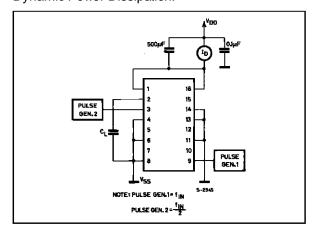
Input Leakage Current.



Input Voltage.

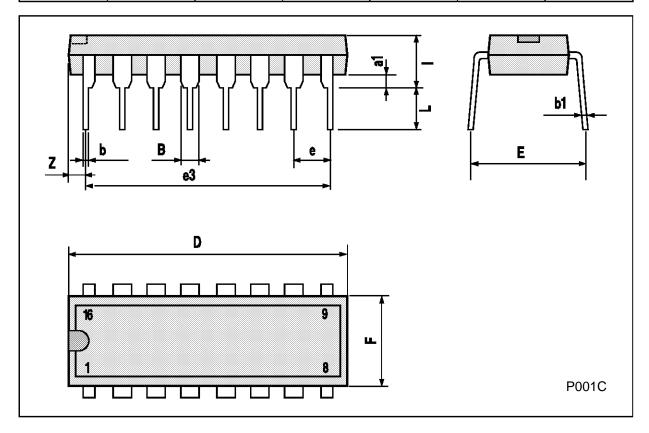


Dynamic Power Dissipation.



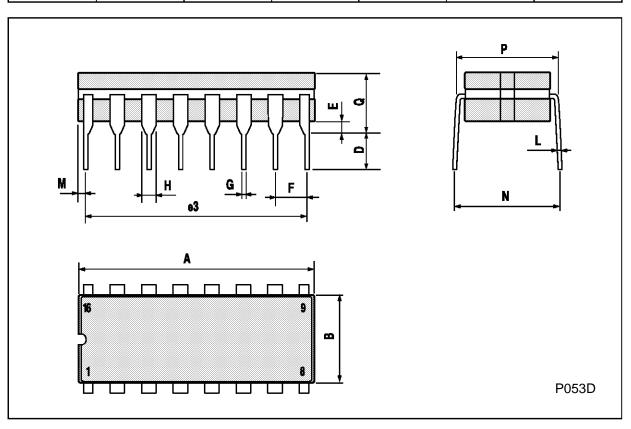
Plastic DIP16 (0.25) MECHANICAL DATA

DIM.		mm		inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
a1	0.51			0.020			
В	0.77		1.65	0.030		0.065	
b		0.5			0.020		
b1		0.25			0.010		
D			20			0.787	
E		8.5			0.335		
е		2.54			0.100		
e3		17.78			0.700		
F			7.1			0.280	
I			5.1			0.201	
L		3.3			0.130		
Z			1.27			0.050	



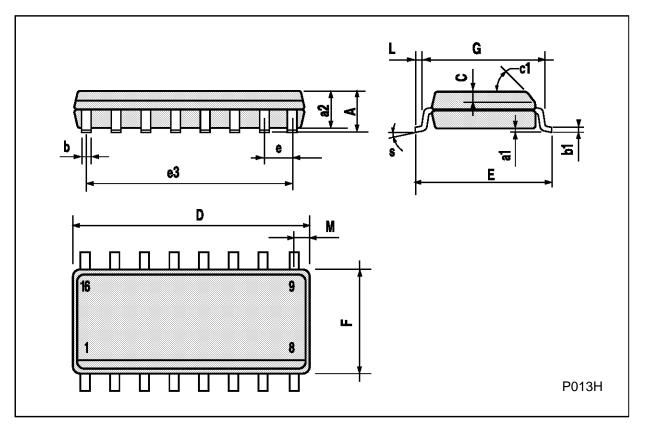
Ceramic DIP16/1 MECHANICAL DATA

DIM.		mm		inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А			20			0.787	
В			7			0.276	
D		3.3			0.130		
E	0.38			0.015			
e3		17.78			0.700		
F	2.29		2.79	0.090		0.110	
G	0.4		0.55	0.016		0.022	
Н	1.17		1.52	0.046		0.060	
L	0.22		0.31	0.009		0.012	
М	0.51		1.27	0.020		0.050	
N			10.3			0.406	
Р	7.8		8.05	0.307		0.317	
Q			5.08			0.200	



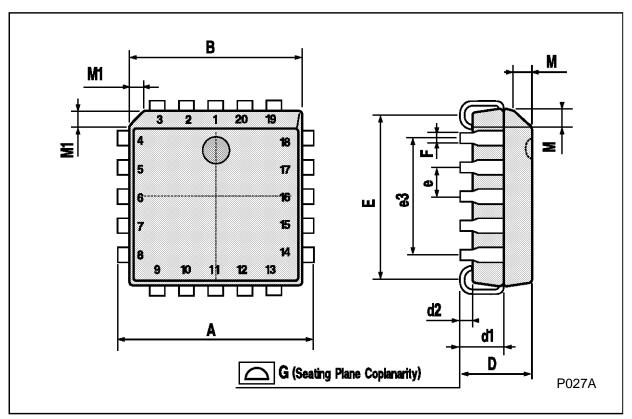
SO16 (Narrow) MECHANICAL DATA

DIM.		mm		inch				
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
А			1.75			0.068		
a1	0.1		0.2	0.004		0.007		
a2			1.65			0.064		
b	0.35		0.46	0.013		0.018		
b1	0.19		0.25	0.007		0.010		
С		0.5			0.019			
c1			45°	(typ.)				
D	9.8		10	0.385		0.393		
Е	5.8		6.2	0.228		0.244		
е		1.27			0.050			
e3		8.89			0.350			
F	3.8		4.0	0.149		0.157		
G	4.6		5.3	0.181		0.208		
L	0.5		1.27	0.019		0.050		
М			0.62			0.024		
S			8° (r	nax.)				



PLCC20 MECHANICAL DATA

DIM.		mm		inch			
5	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	9.78		10.03	0.385		0.395	
В	8.89		9.04	0.350		0.356	
D	4.2		4.57	0.165		0.180	
d1		2.54			0.100		
d2		0.56			0.022		
E	7.37		8.38	0.290		0.330	
е		1.27			0.050		
e3		5.08			0.200		
F		0.38			0.015		
G			0.101			0.004	
М		1.27			0.050		
M1		1.14			0.045		



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